

Reg No.: _____

Name: _____

APJ ABDUL KALAM TECHNOLOGICAL UNIVERSITY
B.Tech Degree S1,S2(S,FE) Examination May 2021 (2015 Scheme)

Course Code: BE101-04

Course Name: INTRODUCTION TO ELECTRONICS ENGINEERING

Max. Marks: 100

Duration: 3 Hours

PART A

Answer all questions, each carries 5 marks

Marks

- | | | |
|---|--|-----|
| 1 | Explain the use of resistors in electronic circuits. List the specifications of a resistor. | (5) |
| 2 | Write the diode equation and explain each term. Explain the effect of temperature in diodes. | (5) |
| 3 | Compare the performance of CB, CE and CC configurations of a transistor. | (5) |
| 4 | Explain the working of a UJT. | (5) |
| 5 | Draw the circuit of a voltage doubler and explain its working. | (5) |
| 6 | With a block diagram explain the working of an SMPS. | (5) |
| 7 | What are Lissajous patterns? How the frequency and phase difference can be measured with Lissajous patterns? | (5) |
| 8 | How the leads of a transistor can be identified by using a multimeter? | (5) |

PART B

Answer six questions, one full question from each module and carries 10 marks.

MODULE I

- | | | |
|---|---|-----|
| 9 | a) Explain the construction and working of an electrolytic capacitor. | (6) |
| | b) Compute the value of capacitors coded as 103 and 4K. | (4) |

OR

- | | | |
|----|--|-----|
| 10 | a) Describe the working of an electromechanical relay. | (6) |
| | b) List the applications of various types of transformers. | (4) |

MODULE II

- | | | |
|----|---|------|
| 11 | Draw the V-I characteristics of a diode and explain its working during forward and reverse biased conditions. | (10) |
|----|---|------|

OR

- 12 a) Differentiate between zener and avalanche breakdown. (5)
b) Explain the working of a Varactor diode. List its applications. (5)

MODULE III

- 13 Find the values of resistances R_1 , R_2 , R_c , R_e for a voltage divider biasing circuit. Given $V_{cc}=10V$, $I_c=1mA$, $\beta=100$ and $V_{CE}=50\%$ of V_{cc} (10)

OR

- 14 Explain the input and output characteristics of an NPN transistor in common emitter configuration. (10)

MODULE IV

- 15 With a neat sketch explain the working and drain characteristics of an N-channel depletion type MOSFET. (10)

OR

- 16 Draw the structure of an SCR and explain its V-I characteristics. (10)

MODULE V

- 17 Draw the circuit and explain the working of a bridge rectifier. Derive the I_{rms} , I_{dc} and ripple factor of a bridge rectifier. (10)

OR

- 18 Explain the working of a negative clamping circuit. Draw a circuit to clamp a given $10V_{pp}$ sine wave negatively by $-4V$ and also draw its input and output waveforms. (10)

MODULE VI

- 19 Draw the block diagram of a Digital Storage Oscilloscope. Explain how amplitude and frequency can be measured using a CRO. (10)

OR

- 20 a) Draw and explain the block diagram of a generalised instrumentation system. (6)
b) Define any four performance parameters of an instrument. (4)
